

[METHOD FOR FABRICATING RAISED SOURCE/DRAIN OF SEMICONDUCTOR DEVICE]

Abstract of Disclosure

A method for fabricating a raised source/drain of a semiconductor device is described. A gate structure is formed on a substrate, and then a source/drain with a shallow-junction is formed in the substrate beside the gate structure. A spacer is formed on the sidewalls of the gate structure. Thereafter, an elevated layer is formed on the gate structure and the source/drain with a shallow junction, wherein the elevated layer formed on the source/drain serves as an elevated source/drain layer.

Figures